

Micropower Undervoltage Sensing Circuits

MC34164, MC33164, NCV33164

The MC34164 series are undervoltage sensing circuits specifically designed for use as reset controllers in portable microprocessor based systems where extended battery life is required. These devices offer the designer an economical solution for low voltage detection with a single external resistor. The MC34164 series features a bandgap reference, a comparator with precise thresholds and built-in hysteresis to prevent erratic reset operation, an open collector reset output capable of sinking in excess of 6.0 mA, and guaranteed operation down to 1.0 V input with extremely low standby current. The MC devices are packaged in 3-pin TO-92 (TO-226AA), micro size TSOP-5, 8-pin SOIC-8 and Micro8 surface mount packages. The NCV device is packaged in SOIC-8.

Applications include direct monitoring of the 3.0 V or 5.0 V MPU/logic power supply used in appliance, automotive, consumer, and industrial equipment.

Features

- Temperature Compensated Reference
- Monitors 3.0 V (MC34164-3) or 5.0 V (MC34164-5) Power Supplies
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 6.0 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation With 1.0 V Input
- Extremely Low Standby Current: As Low as 9.0 μ A
- Economical TO-92 (TO-226AA), TSOP-5, SOIC-8 and Micro8 Surface Mount Packages
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes
- These Devices are Pb-Free and are RoHS Compliant

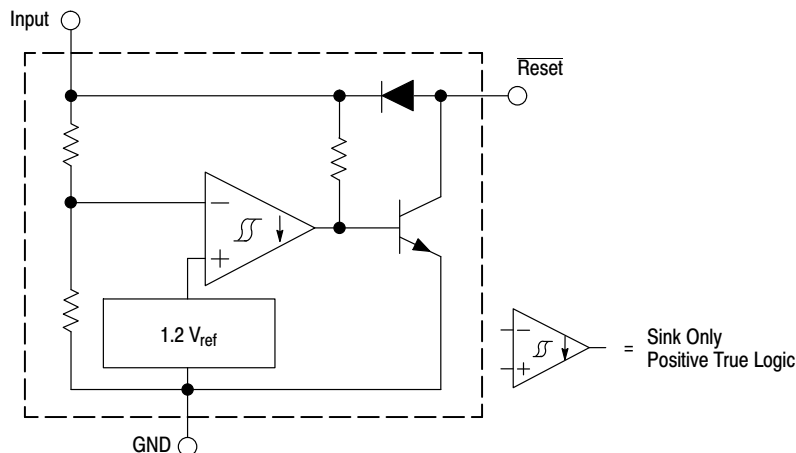
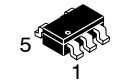
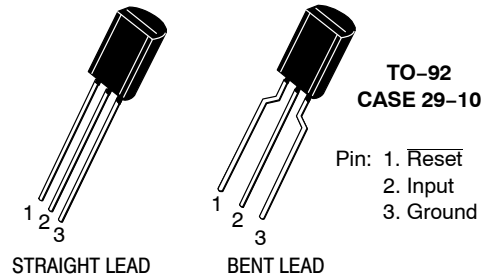


Figure 1. Representative Block Diagram

This device contains 28 active transistors.



**TSOP-5
SN SUFFIX
CASE 483**

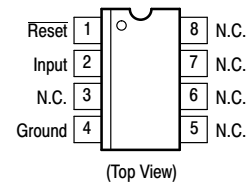


**SOIC-8
D SUFFIX
CASE 751**



**Micro8
DM SUFFIX
CASE 846A**

PIN CONNECTIONS



TSOP-5

Pin 1. Ground
2. Input
3. Reset
4. NC
5. NC

TO-92

Pin 1. Reset
2. Input
3. Ground

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 7.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 8 of this data sheet.

MC34164, MC33164, NCV33164

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_{in}	Power Input Supply Voltage	-1.0 to 12	V
V_O	$\overline{\text{Reset}}$ Output Voltage	-1.0 to 12	V
I_{Sink}	$\overline{\text{Reset}}$ Output Sink Current	Internally Limited	mA
IF	Clamp Diode Forward Current, Reset to Input Pin (Note 1)	100	mA
P_D $R_{\theta JA}$	Power Dissipation and Thermal Characteristics P Suffix, Plastic Package Maximum Power Dissipation @ $T_A = 25^\circ\text{C}$ Thermal Resistance, Junction-to-Air	700 178	mW $^\circ\text{C/W}$
P_D $R_{\theta JA}$	D Suffix, Plastic Package Maximum Power Dissipation @ $T_A = 25^\circ\text{C}$ Thermal Resistance, Junction-to-Air	700 178	mW $^\circ\text{C/W}$
P_D $R_{\theta JA}$	DM Suffix, Plastic Package Maximum Power Dissipation @ $T_A = 25^\circ\text{C}$ Thermal Resistance, Junction-to-Air	520 240	mW $^\circ\text{C/W}$
T_J	Operating Junction Temperature	+150	$^\circ\text{C}$
T_A	Operating Ambient Temperature Range MC34164 Series MC33164 Series, NCV33164	0 to +70 - 40 to +125	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	- 65 to +150	$^\circ\text{C}$
ESD	Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Machine Model (MM)	4000 200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

MC34164-3, MC33164-3 SERIES, NCV33164-3

ELECTRICAL CHARACTERISTICS (For typical values $T_A = 25^\circ\text{C}$, for min/max values T_A is the operating ambient temperature range that applies [Notes 2 & 3], unless otherwise noted.)

Symbol	Characteristic	Min	Typ	Max	Unit
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COMPARATOR

V_{IH}	Threshold Voltage				V
V_{IL}	High State Output (V_{in} Increasing)	2.55	2.71	2.80	
V_H	Low State Output (V_{in} Decreasing)	2.55	2.65	2.80	
V_H	Hysteresis ($I_{Sink} = 100 \mu\text{A}$)	0.03	0.06	-	

RESET OUTPUT

V_{OL}	Output Sink Saturation ($V_{in} = 2.4 \text{ V}$, $I_{Sink} = 1.0 \text{ mA}$) ($V_{in} = 1.0 \text{ V}$, $I_{Sink} = 0.25 \text{ mA}$)	- -	0.14 0.1	0.4 0.3	V
I_{Sink}	Output Sink Current (V_{in} , $\overline{\text{Reset}} = 2.4 \text{ V}$)	6.0	12	30	mA
$I_R(\text{leak})$	Output Off-State Leakage (V_{in} , $\overline{\text{Reset}} = 3.0 \text{ V}$) (V_{in} , $\overline{\text{Reset}} = 10 \text{ V}$)	- -	0.02 0.02	0.5 1.0	μA
V_F	Clamp Diode Forward Voltage, Reset to Input Pin ($I_F = 5.0 \text{ mA}$)	0.6	0.9	1.2	V

TOTAL DEVICE

V_{in}	Operating Input Voltage Range	1.0 to 10	-	-	V
I_{in}	Quiescent Input Current $V_{in} = 3.0 \text{ V}$ $V_{in} = 6.0 \text{ V}$	- -	9.0 24	15 40	μA

- Maximum package power dissipation limits must be observed.
- Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
- $T_{low} = 0^\circ\text{C}$ for MC34164
= - 40 $^\circ\text{C}$ for MC33164, NCV33164
 $T_{high} = +70^\circ\text{C}$ for MC34164
= +125 $^\circ\text{C}$ for MC33164, NCV33164

MC34164, MC33164, NCV33164

MC34164-5, MC33164-5 SERIES, NCV33164-5

ELECTRICAL CHARACTERISTICS (For typical values $T_A = 25^\circ\text{C}$, for min/max values T_A is the operating ambient temperature range that applies [Notes 5 & 6], unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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COMPARATOR

Threshold Voltage					V
High State Output (V_{in} Increasing)	V_{IH}	4.15	4.33	4.45	
Low State Output (V_{in} Decreasing)	V_{IL}	4.15	4.27	4.45	
Hysteresis ($I_{Sink} = 100\ \mu\text{A}$)	V_H	0.02	0.09	–	

RESET OUTPUT

Output Sink Saturation ($V_{in} = 4.0\ \text{V}$, $I_{Sink} = 1.0\ \text{mA}$) ($V_{in} = 1.0\ \text{V}$, $I_{Sink} = 0.25\ \text{mA}$)	V_{OL}	– –	0.14 0.1	0.4 0.3	V
Output Sink Current (V_{in} , $\text{Reset} = 4.0\ \text{V}$)	I_{Sink}	7.0	20	50	mA
Output Off-State Leakage (V_{in} , $\text{Reset} = 5.0\ \text{V}$) (V_{in} , $\text{Reset} = 10\ \text{V}$)	$I_R(\text{leak})$	– –	0.02 0.02	0.5 2.0	μA
Clamp Diode Forward Voltage, Reset to Input Pin ($I_F = 5.0\ \text{mA}$)	V_F	0.6	0.9	1.2	V

TOTAL DEVICE

Operating Input Voltage Range	V_{in}	1.0 to 10	–	–	V
Quiescent Input Current $V_{in} = 5.0\ \text{V}$ $V_{in} = 10\ \text{V}$	I_{in}	– –	12 32	20 50	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Maximum package power dissipation limits must be observed.
- Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
- $T_{low} = 0^\circ\text{C}$ for MC34164 $T_{high} = +70^\circ\text{C}$ for MC34164
 $= -40^\circ\text{C}$ for MC33164, NCV33164 $= +125^\circ\text{C}$ for MC33164, NCV33164
- NCV prefix is for automotive and other applications requiring site and change control.

TYPICAL CHARACTERISTICS

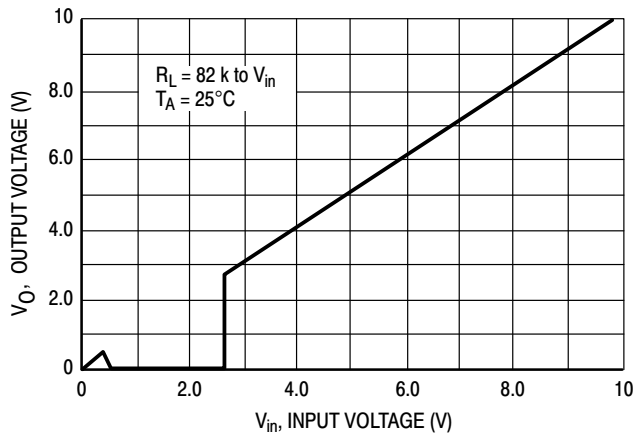


Figure 2. MC3X164-3 $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

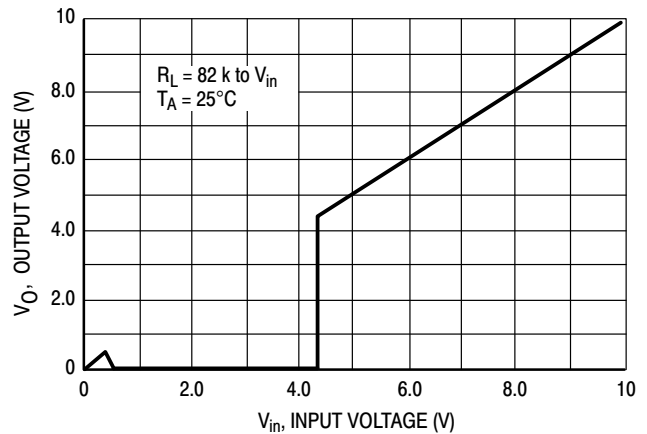


Figure 3. MC3X164-5 $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

TYPICAL CHARACTERISTICS (continued)

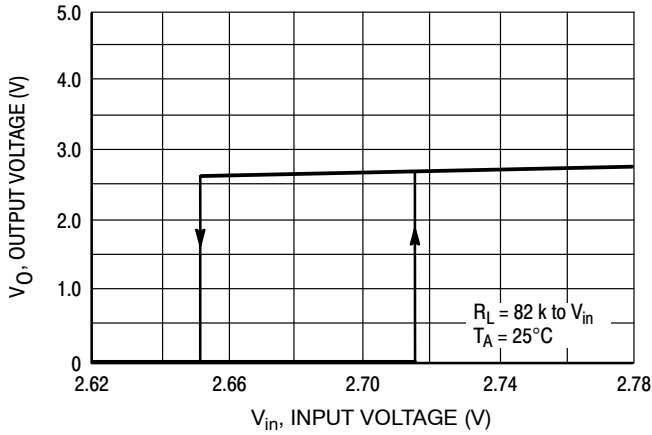


Figure 4. MC3X164-3 Reset Output Voltage versus Input Voltage

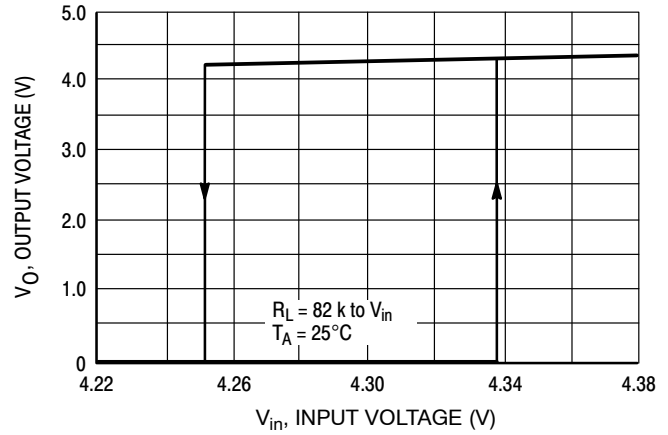


Figure 5. MC3X164-5 Reset Output Voltage versus Input Voltage

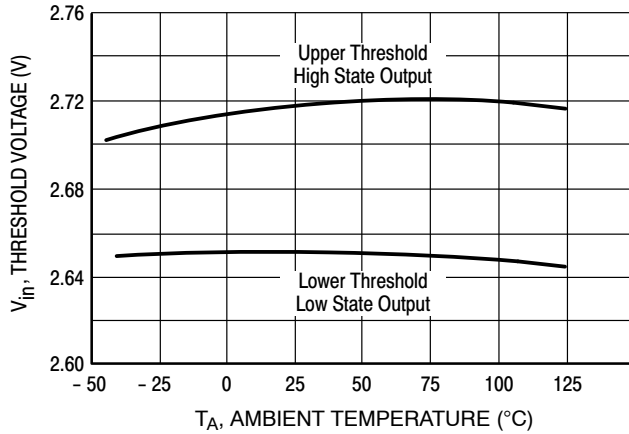


Figure 6. MC3X164-3 Comparator Threshold Voltage versus Temperature

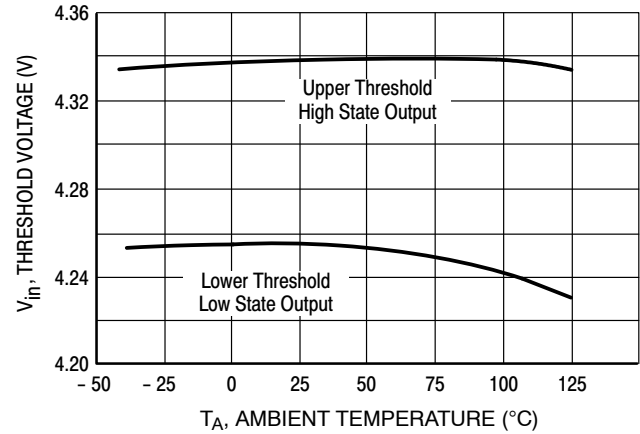


Figure 7. MC3X164-5 Comparator Threshold Voltage versus Temperature

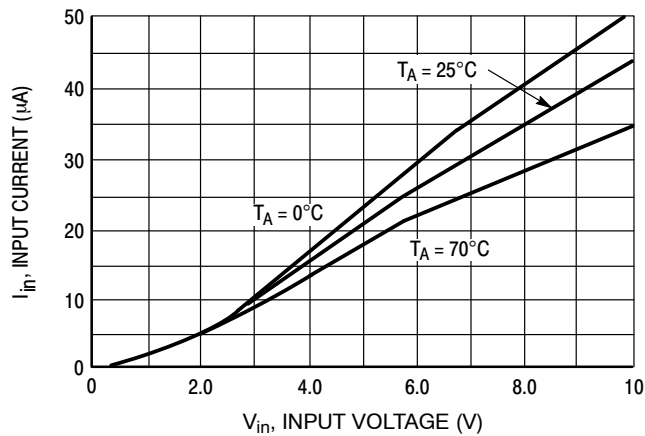


Figure 8. MC3X164-3 Input Current versus Input Voltage

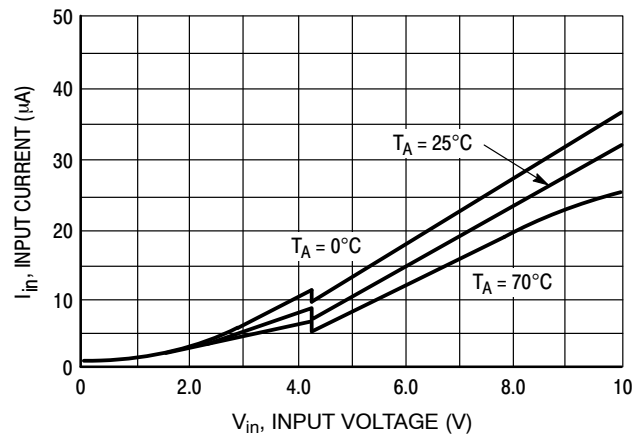


Figure 9. MC3X164-5 Input Current versus Input Voltage

TYPICAL CHARACTERISTICS (continued)

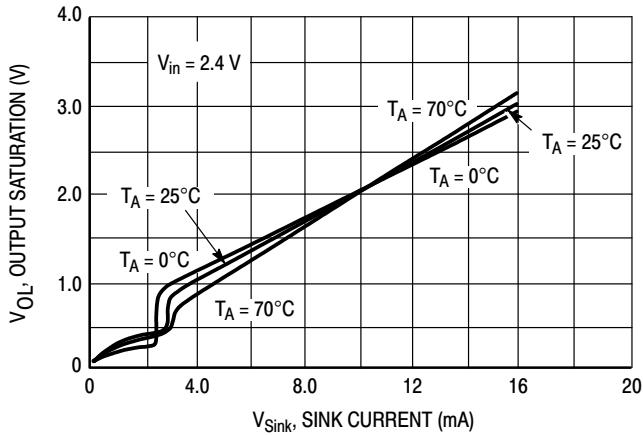


Figure 10. MC3X164-3 $\overline{\text{Reset}}$ Output Saturation versus Sink Current

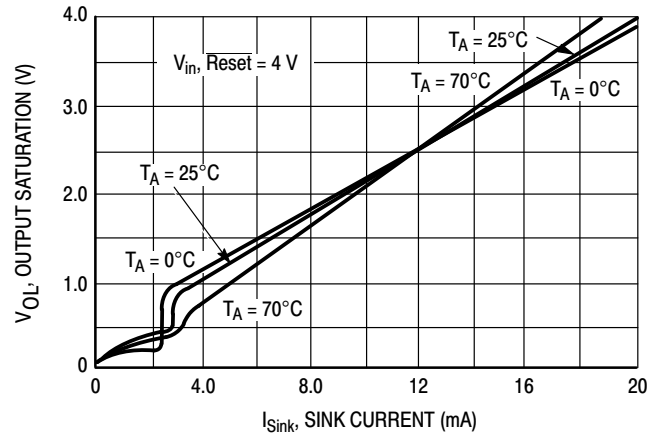


Figure 11. MC3X164-5 $\overline{\text{Reset}}$ Output Saturation versus Sink Current

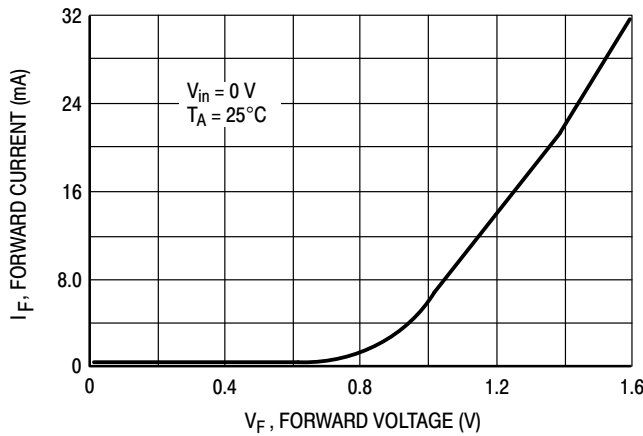


Figure 12. Clamp Diode Forward Current versus Voltage

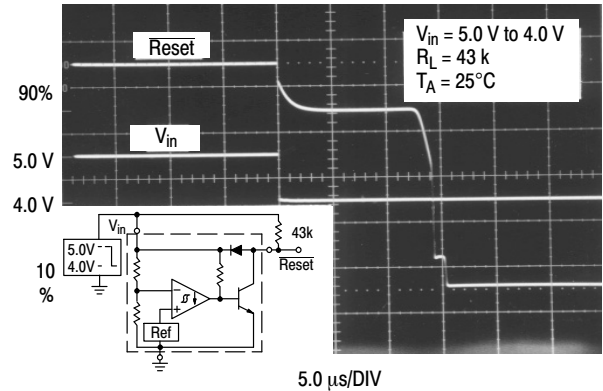
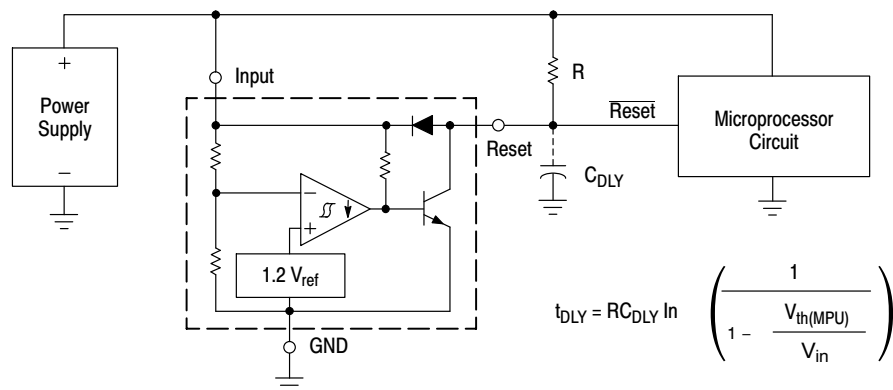


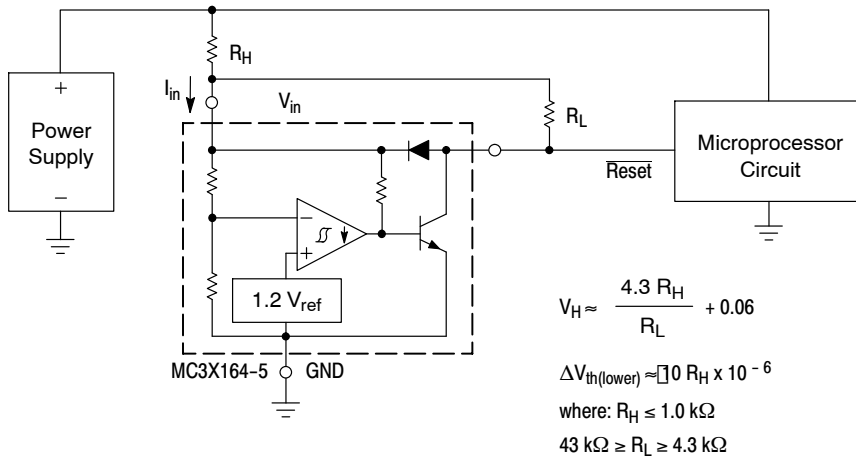
Figure 13. $\overline{\text{Reset}}$ Delay Time (MC3X164-5 Shown)



A time delayed reset can be accomplished with the addition of C_{DLY} . For systems with extremely fast power supply rise times (< 500 ns) it is recommended that the RC_{DLY} time constant be greater than $5.0 \mu\text{s}$. $V_{th(MPU)}$ is the microprocessor reset input threshold.

Figure 14. Low Voltage Microprocessor Reset

MC34164, MC33164, NCV33164



Test Data			
V_H (mV)	ΔV_{th} (mV)	R_H (Ω)	R_L (k Ω)
60	0	0	43
103	1.0	100	10
123	1.0	100	6.8
160	1.0	100	4.3
155	2.2	220	10
199	2.2	220	6.8
280	2.2	220	4.3
262	4.7	470	10
306	4.7	470	8.2
357	4.7	470	6.8
421	4.7	470	5.6
530	4.7	470	4.3

Comparator hysteresis can be increased with the addition of resistor R_H . The hysteresis equation has been simplified and does not account for the change of input current I_{in} as V_{in} crosses the comparator threshold (Figure 8). An increase of the lower threshold $\Delta V_{th(lower)}$ will be observed due to I_{in} which is typically 10 μA at 4.3 V. The equations are accurate to $\pm 10\%$ with R_H less than 1.0 k Ω and R_L between 4.3 k Ω and 43 k Ω .

Figure 15. Low Voltage Microprocessor Reset With Additional Hysteresis (MC3X164-5 Shown)

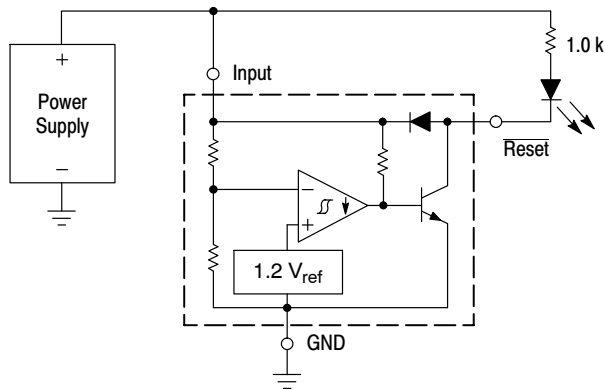


Figure 16. Voltage Monitor

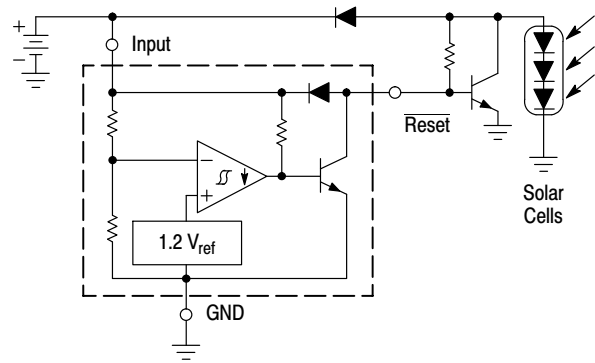
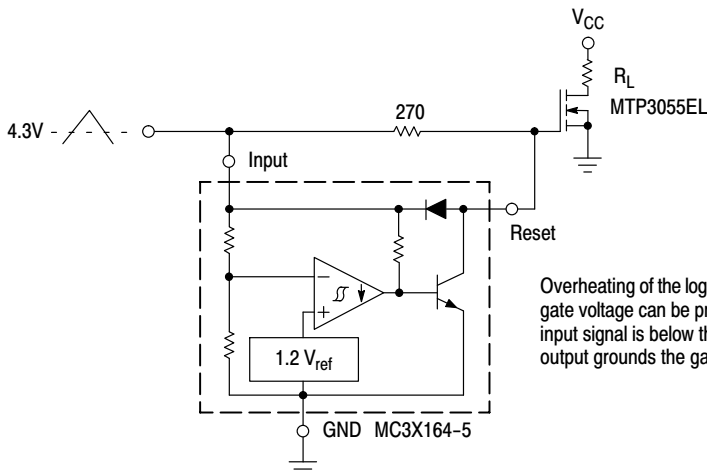


Figure 17. Solar Powered Battery Charger



Overheating of the logic level power MOSFET due to insufficient gate voltage can be prevented with the above circuit. When the input signal is below the 4.3 V threshold of the MC3X164-5, its output grounds the gate of the L² MOSFET.

Figure 18. MOSFET Low Voltage Gate Drive Protection Using the MC3X164-5

MC34164, MC33164, NCV33164

ORDERING INFORMATION

Device	Package	Shipping†
MC33164D-3G	SOIC-8 (Pb-Free)	98 Units / Rail
MC33164D-3R2G	SOIC-8 (Pb-Free)	2,500 Units / Tape & Reel
MC33164DM-3R2G	Micro8 (Pb-Free)	4,000 Units / Tape & Reel
MC33164P-3G	TO-92 (Pb-Free)	2,000 Units / Box
MC33164P-3RPG	TO-92 (Pb-Free)	2,000 Units / Pack
MC33164D-5G	SOIC-8 (Pb-Free)	98 Units / Rail
MC33164D-5R2G	SOIC-8 (Pb-Free)	2,500 Units / Tape & Reel
NCV33164D-5R2G*	SOIC-8 (Pb-Free)	
MC33164DM-5R2G	Micro8 (Pb-Free)	4,000 Units / Tape & Reel
MC33164P-5G	TO-92 (Pb-Free)	2,000 Units / Box
MC33164P-5RAG	TO-92 (Pb-Free)	2,000 Units / Tape & Reel
MC33164P-5RPG	TO-92 (Pb-Free)	2,000 Units / Pack
MC34164D-3R2G	SOIC-8 (Pb-Free)	2,500 Units / Tape & Reel
MC34164D-5R2G	SOIC-8 (Pb-Free)	2,500 Units / Tape & Reel
MC34164P-5G	TO-92 (Pb-Free)	2,000 Units / Box

DISCONTINUED (Note 8)

NCV33164D-3R2G*	SOIC-8 (Pb-Free)	2,500 Units / Tape & Reel
MC33164P-3RAG	TO-92 (Pb-Free)	2,000 Units / Tape & Reel
MC34164D-3G	SOIC-8 (Pb-Free)	98 Units / Rail
MC34164DM-3R2G	Micro8 (Pb-Free)	4,000 Units / Tape & Reel
MC34164P-3G	TO-92 (Pb-Free)	2,000 Units / Box
MC34164P-3RPG	TO-92 (Pb-Free)	2,000 Units / Pack
MC34164D-5G	SOIC-8 (Pb-Free)	98 Units / Rail
MC34164DM-5R2G	Micro8 (Pb-Free)	4,000 Units / Tape & Reel
MC34164SN-5T1G	TSOP-5 (Pb-Free)	3,000 Units / Tape & Reel
MC34164P-5RAG	TO-92 (Pb-Free)	2,000 Units / Tape & Reel
MC34164P-5RPG	TO-92 (Pb-Free)	2,000 Units / Pack

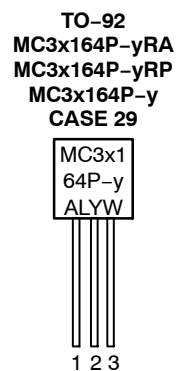
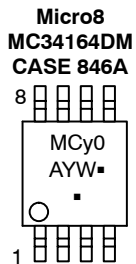
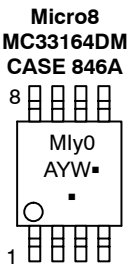
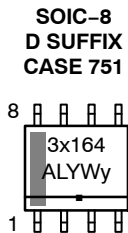
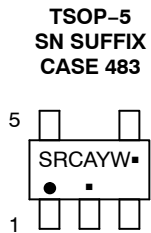
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

*NCV33164: $T_{low} = -40^{\circ}\text{C}$, $T_{high} = +125^{\circ}\text{C}$. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

8. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

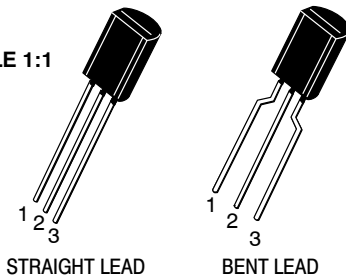
MC34164, MC33164, NCV33164

PIN CONNECTIONS AND MARKING DIAGRAMS



SRC = Device Code
 x = Device Number 3 or 4
 y = Suffix Number 3 or 5
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free

SCALE 1:1



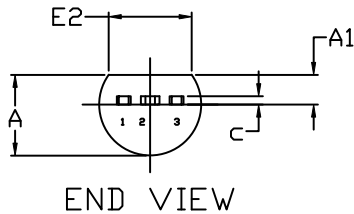
STRAIGHT LEAD

BENT LEAD

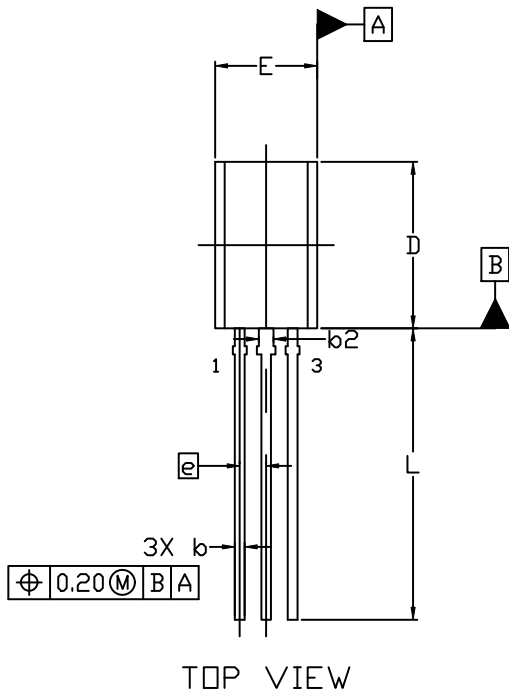
TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE D

DATE 05 MAR 2021

STRAIGHT LEAD



END VIEW



TOP VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	1.27 BSC		
L	13.80	14.00	14.20

STYLES AND MARKING ON PAGE 3

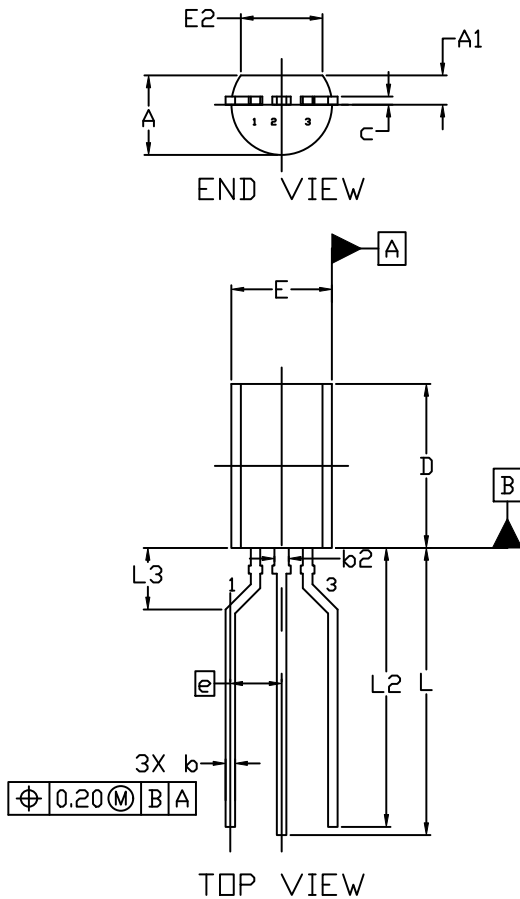
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DESCRIPTION:	TO-92 (TO-226) 1 WATT	PAGE 1 OF 3

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TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE D

DATE 05 MAR 2021

FORMED LEAD



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND $b2$ DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION $b2$ LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3	3.00 REF		

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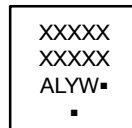
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CASE 29-10
ISSUE D

DATE 05 MAR 2021

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. V _{CC} 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

**GENERIC
MARKING DIAGRAM***



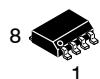
XXXX = Specific Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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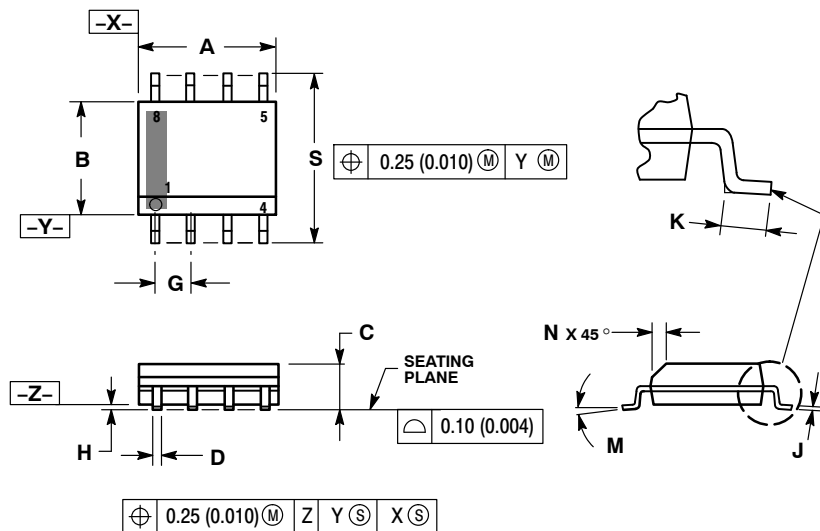
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SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

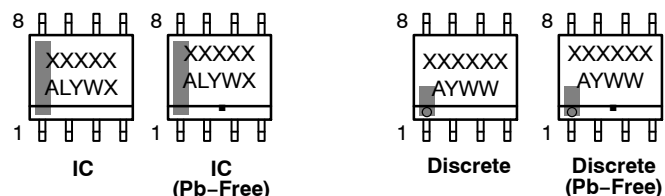
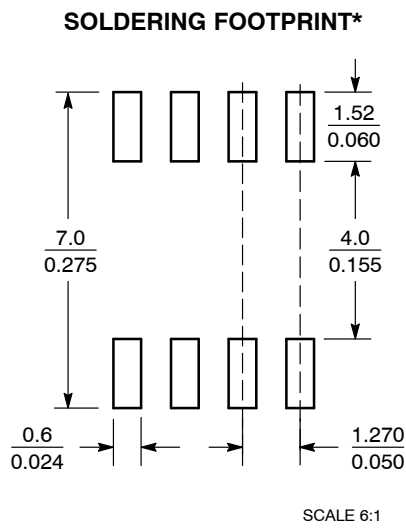


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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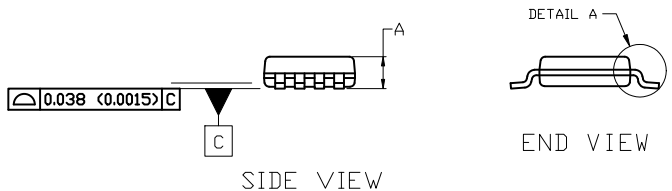
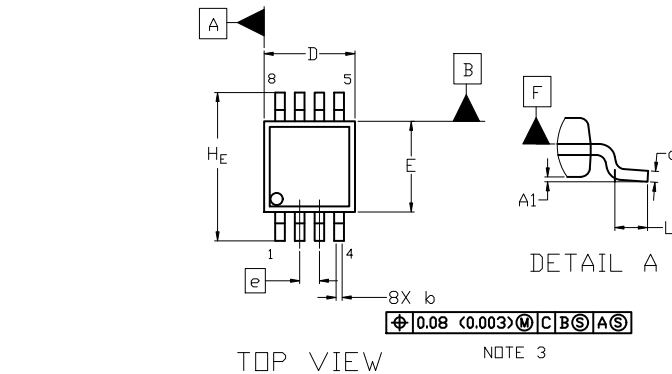
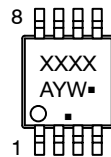
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SCALE 2:1

Micro8
CASE 846A-02
ISSUE K

DATE 16 JUL 2020


GENERIC
MARKING DIAGRAM*


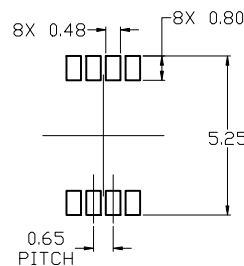
XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM-10.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H _E	4.75	4.90	5.05
L	0.40	0.55	0.70

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:

1. N-SOURCE
2. N-GATE
3. P-SOURCE
4. P-GATE
5. P-DRAIN
6. P-DRAIN
7. N-DRAIN
8. N-DRAIN

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